



High-Side N-Channel Switch with Current Limit

FEATURES

- User Set Over Current Limit From 400 mA to 2.4 A
- Low $r_{\mbox{DS(on)}}$ 45 m Ω (max) at 25 $^{\circ}\mbox{C}$
- Fault Indicator
- Under Voltage Lockout

APPLICATIONS

- · Notebook Computers Power Management
- USB Power Distribution
- · Hot Plug In Power Supplies
- Power Supply/Load Protection
- · Battery-Charger Circuits



RoHS*

DESCRIPTION

The Si4779CY n-channel high-side switch combines a low $r_{DS(on)}$ MOSFET switch with a user set, pulse gate control (PGC) based current limit. This switch is designed to protect the system power supply from overloads and short circuit conditions in applications such as USB. The PGC based approach to the current limiter provides the additional benefit of keeping the

thereby eliminating the need for thermal shutdown. The low quiescent current makes the Si4779CY ideal for use in battery powered devices. The Si4779CY operates on both 3 V and 5 V busses, and is packaged in the LITTLE FOOT® SO-8 package.

MOSFET junction temperature within specification,

FUNCTIONAL BLOCK DIAGRAM

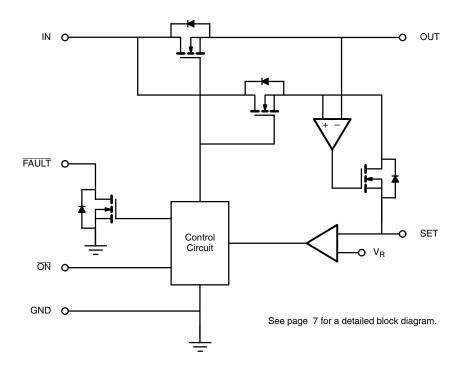


FIGURE 1.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Voltage, IN to GND	V _{IN}	- 0.3 to 7	v		
Voltage, ON	V _{ON}	- 0.3 to 7			
Continuous Drain Current /T 150 °C)8	T _A = 25 °C	l _D	2.4	Α	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		2.4		
Maximum Power Dissipation ^a T _A = 70 °C		P_{D}	0.65	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 65 to 125	°C	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS					
Parameter	Symbol	Typical	Unit		
Voltage, IN to GND	V _{IN}	3.0 to 5.0			
Voltage, ON or FAULT to GND	V _{ON} , V _{FAULT}	0 to 5.0	V		
Operating Temperature Range	T _A	0 to 85	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	Steady State	R _{thJA}	98	120	°C/W	
Junction-to-Foot (Drain) ^b	Sieduy Sidie	R _{thJF}	37	46	C/VV	

a. Surface mounted on 1" x 1" FR4 board, 0.062" thick, 2-oz copper double sided.
b. Junction-to-foot thermal impedance represents the effective thermal impedance of all heat carrying leads in parallel and is intended for use in conjunction with the thermal impedance of the PC board pads to ambient (R_{thJA} = R_{thJF} + R_{thPCB-A}). It can also be used to estimate chip temperature if power dissipation and the lead temperature of a heat carrying (drain) lead is known.





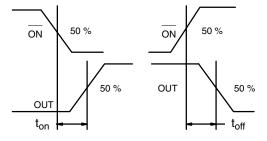
SPECIFICATIONS							
Parameter	Symbol	Test Conditions Unless Specified	Limits				
Parameter		$T_A = 25 ^{\circ}C, V_{IN} = 5 V$		Typ ^a	Max	Unit	
Basic Operations							
Operating Voltage	V _{IN}		2.7		5.5	V	
On-State Resistance	r _{DS(on)}	V _{IN} = 4.75 V, I _D = 2 A		0.035	0.045	.0	
On State Hedicianse		V _{IN} = 3.0 V, I _D = 2 A		0.045	0.055	32	
Supply Current	I _{SUP(off)}	$\overline{ON} = IN, V_{IN} = 5.5 V, V_{OUT} = 0 V$			2	μΑ	
Supply Suitem	I _{SUP(on)}	$\overline{ON} = GND$, $V_{IN} = V_{OUT} = 5.5 \text{ V}$, $I_{OUT} = 0 \text{ V}$			70		
ON Input Low Voltage	V_{ONL}	V _{IN} = 2.7 V to 5.5 V			0.8		
ON Input High Voltage	V _{ONH}	V _{IN} = 2.7 V to 3.6 V	o 3.6 V 2.0			V	
ON Input High Voltage	VONH	V _{IN} = 4.5 V to 5.5 V	2.4				
ON Input Current	I _{ON}	V _{ON} = 5.5 V		0.01	± 1	μΑ	
Protection							
Over Current Limit Range ^b	I _{LIMIT}	Tolerance = ± 20 %, V _{IN} = 5 V	0.4		2.4	Α	
Under Voltage Lockout (rising edge)	UVLO _{rise}		2.0		4.0		
Under Voltage Lockout (falling edge)	UVLO _{fall}		2.0	2.3	2.6	V	
Under Voltage Hysteresis	ΔUVLO			0.1		v	
FAULT Output Voltage Low ^b	V _{FAULT}	I _{SINK} = 100 μA			0.4		
FAULT Logic Output Leakage Current	I _{FL}	V _{IN} = V _{FAULT} = 5.5 V		0.01	1	μΑ	
Dynamic ^b							
Turn-On Time	t _{on}	$V_{IN} = 5 \text{ V, R}_{I} = 11 \Omega, C_{I} = 40 \mu\text{F}$		3		- ms	
Rise Time	t _r	- ν _{IN} – 5 ν, τις – τι 22, Ος – 40 μι		3.5		1115	
Turn-Off Time	t _{off}	V _{IN} = 5 V, I _{OUT} = 500 mA		1.5			
Fall Time	t _f			0.5		μs	
Cycle Time	t _{cyc}	$V_{IN} = 5 \text{ V}, R_{L} = 0.5 \Omega$		8		ms	

Notes

- a. Typical values at $T_A = 25$ °C are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- b. Guaranteed by design. Derived from I_{SET} current ratio, current-limit amplifier and external set resistor accuracy.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TIMING DIAGRAMS





90 %

OUT 10 %

 t_{rise}

90 %

OUT

10 %

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TIMING DIAGRAMS

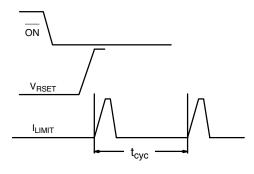


FIGURE 4.

TYPICAL CHARACTERISTICS 25 °C, unless noted

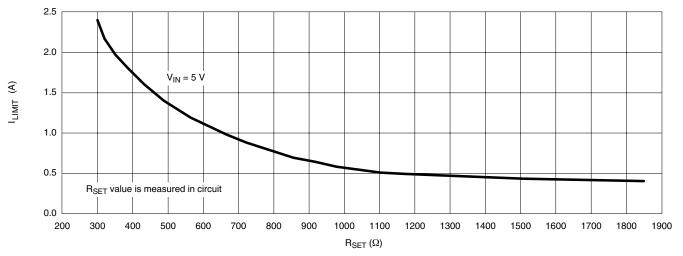


FIGURE 5. $R_{\rm SET}$ vs. $I_{\rm LIMIT}$

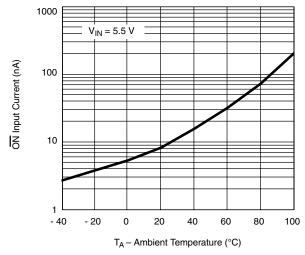


FIGURE 6. Supply Current, Output Disable vs. Ambient Temperature Over Operating Voltage

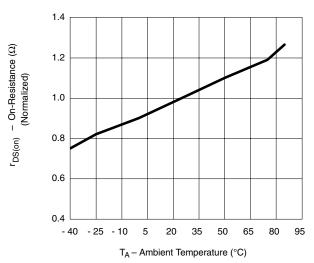
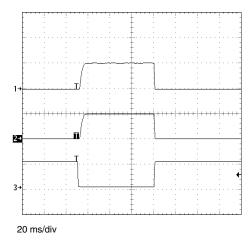


FIGURE 7. Normalized On-Resistance vs. Ambient Temperature



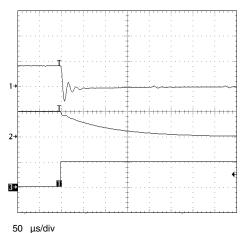


TYPICAL WAVEFORMS $V_{IN} = 5 \text{ V}$, $T_A = 25 \,^{\circ}\text{C}$, unless otherwise noted



CH1: I_{OUT} , 2 A/div CH2: V_{OUT} , 5 V/div, C_L = 47 μ F CH3: \overline{ON} , 5 V/div

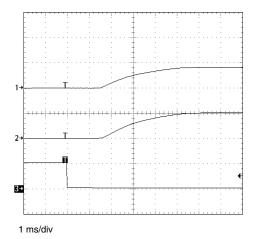
FIGURE 8. Switch Turn-ON/OFF Time



CH1: I_{OUT} , 0.5 A/div CH2: V_{OUT} , 5 V/div, C_L = 10 μ F CH3: \overline{ON} , 5 V/div

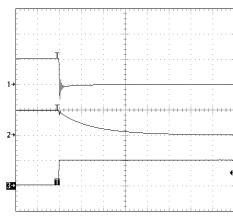
NOTE: Discharge time based primarily on external R and C

FIGURE 10. Switch Turn-OFF Time



CH1: I_{OUT} , 0.5 A/div CH2: V_{OUT} , 5 V/div, C_L = 10 μ F CH3: \overline{ON} , 5 V/div

FIGURE 9. Switch Turn-ON Time



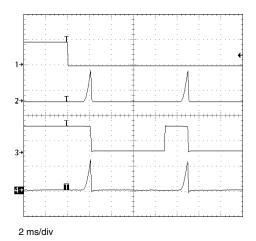
200 μs/div

CH1: I_{OUT} , 0.5 A/div CH2: V_{OUT} , 5 V/div, C_L = 150 μ F CH3: \overline{ON} , 5 V/div

NOTE: Discharge time based primarily on external R and C

FIGURE 11. Switch Turn-OFF Time

TYPICAL WAVEFORMS $V_{IN} = 5 \text{ V}$, $T_A = 25 \,^{\circ}\text{C}$, unless otherwise noted

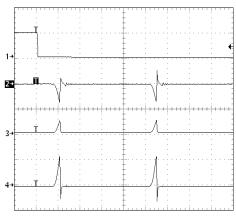


CH1: \overline{ON} , 5 V/div

CH2: V_{OUT} , 5 V/div, R_L = 0.5 Ω , C_L = 47 μF CH3: FAULT, 5 V/div

CH4: I_{OUT}, 1 A/div

FIGURE 12. FAULT to Short Response (t_{cyc})



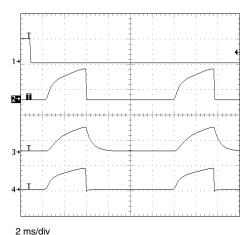
2 ms/div

CH1: \overline{ON} , 5 V/div CH2: PS Droops, 50 mV/div, Offset = 5 V CH3: V_{OUT} , 1 V/div, R_L = 0.5 Ω , C_L = 100 μF

CH4: I_{OUT}, 0.5 A/div

NOTE: Special test with 820- μF capacitor at PS and $R_{\mbox{\footnotesize SET}}$ setup for 0.5 A.

FIGURE 14. Power Supply Droops vs. Short

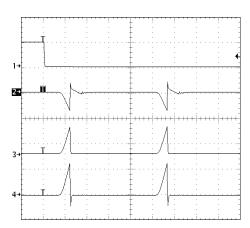


CH1: \overline{ON} , 5 V/div

CH2: V_{RESET} , 500 mV/div CH3: V_{OUT} , 5 V/div, R_L = 5.6 Ω , C_L = 100 μF

CH4: I_{OUT}, 1 A/div

FIGURE 13. V_{RESET} to Over Current Response



2 ms/div

CH1: \overline{ON} , 5 V/div CH2: PS Droops, 100 mV/div, Offset = 5 V CH3: V_{OUT} , 1 V/div, R_L = 0.5 Ω , C_L = 100 μF

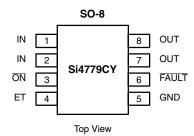
CH4: I_{OUT}, 2 A/div

NOTE: Special test with 820- μF capacitor at PS and R_SET setup for 2.4 A.

FIGURE 15. Power Supply Droops vs. Short



PIN CONFIGURATION



Ordering Information: Si4779CY-T1 Si4779CY-T1-E3 (Lead (Pb)-free)

PIN	PIN DESCRIPTION					
Pin	Symbol	Description				
1, 2	IN	Input. N-channel MOSFET drain, bypass IN with a 100 μF capacitor to GND.				
3	ŌN	Active-low switch-on input, logic low turns switch on. \overline{ON} needs to be connected to V_{IN} during power up, then connect to GND to activate the switch after power up.				
4	SET	Current-limit input. A resistor from SET to GND sets the current limit for the switch.				
5	GND	Ground				
6	FAULT	Fault indicator output. This open drain output goes low when the circuit is in current limit or in short circuit protection mode.				
7, 8	OUT	Switch output. N-channel MOSFET source.				

DETAILED BLOCK DIAGRAM

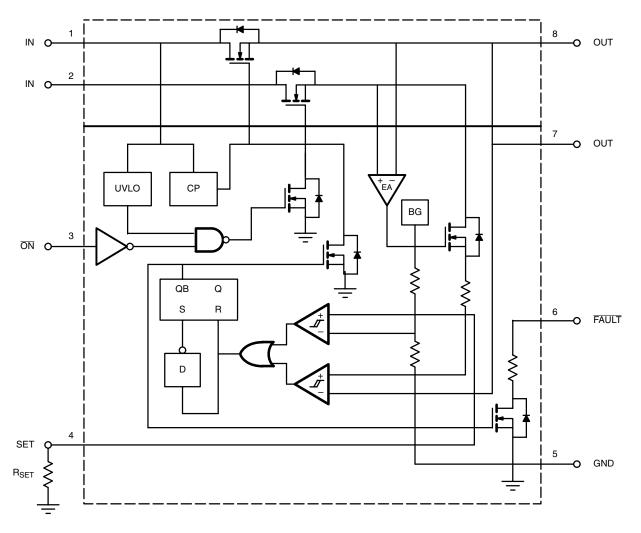


FIGURE 16.

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DETAILED DESCRIPTION

The SI4779CY limits the output current to a user-defined level. When the output current passes through the main switch a fraction of this current passes through a replica switch and $R_{\rm SFT}$.

 R_{SET} is an external sense resistor used to set the level of the over current limit; the over current limit should be set between 0.4 A and 2.4 A (see graph for R_{SET} value vs. current limit). The circuit shuts down the switch when the current flowing through the switch exceeds Ilimit. After a short period of time, the circuit will slowly turn on the switch again. The length of time off is based on aver-

age power consumption, which is designed to be kept under 500 mW.

If the output is shorted, the circuit will go into an on-off cycle to protect the switch and to prevent the battery from draining down.

The fault output ($\overline{\text{FAULT}}$) goes low when the circuit is in over current limit or short circuit protection mode. A 100 k Ω pull-up resistor from $\overline{\text{FAULT}}$ to IN provides a logic-control signal.

APPLICATIONS DIAGRAM

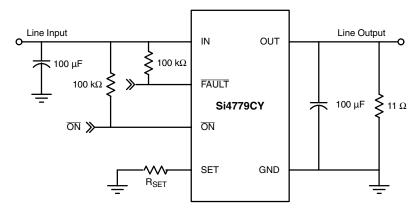


FIGURE 17.

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